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Kawaletz

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(54) **METHOD FOR TESTING A CMOS TRANSISTOR**
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See application file for complete search history.

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(57) **ABSTRACT**
A method for testing a CMOS transistor with an electrical testing unit, the CMOS transistor being formed in a semiconductor substrate of a semiconductor wafer. A plurality of CMOS transistors are formed on the semiconductor wafer and the electrical testing unit has a support plate and a metal layer formed on the support plate. The CMOS transistor having a first terminal contact, a second terminal contact and a third terminal contact, the second terminal contact configured as an electrically open control contact and in a process step the metal layer is positioned above the semiconductor wafer over the control contact and a potential difference between the first terminal contact and a third terminal contact is generated. The control contact is capacitively coupled by applying a drive potential to the metal layer, and the function of the CMOS transistor is tested by measuring an electrical variable dependent on the capacitive coupling.

17 Claims, 2 Drawing Sheets

